PCI	PCN Number: PCN#2024					000.2	2				F	PCN D	ate:	April 14, 2024	
Titl	le:	Qualifica	ation	of Cu	as an	alteri	nate bo	ond wi	re for sele	ct d	evi	ces			
Cus	stom	er Conta	ct:	Chan	ge Mai	nage	ment T	eam	Dept:	Qu	alit	y Servi	ices		
Pro	pose	ed 1 <sup>st</sup> Shi	ip Da	ate:	Octob 2024	er 1	1,	Sample Requests accepted until:					14, 2024*		
*Sa	ampl	e reques	sts re	eceive	d afte	r Ma	y 14,	2024	will not l	oe s	up	ported	l.		
	Asse	embly Site	e				Design					Wafer Bump Material			
	Asse	embly Pro	cess				Data	Sheet				Wafer Bump Process			
Assembly Materials							Part i	numbe	r change			Wafer Fab Site			
	Mechanical Specification						Test Site					Wafer Fab Material			
	Packing/Shipping/Labeling						Test Process				Wafer Fab Process				
							-		••					-	

## **PCN Details**

# **Description of Change:**

This PCN is to inform of an alternative bond qualification for the devices in the product affected section as follows:

What	Current	Additional
Current Bond wire, Diameter	Au, 0.96 mil (die to die) + 1.0 mil Cu (die to leadframe)	Cu, 0.8 mil (all)

## **Reason for Change:**

Continuity of supply.

- 1) To align with world technology trends and use wiring with enhanced mechanical and electrical properties
- 2) Maximize flexibility within our Assembly/Test production sites.
- 3) Cu is easier to obtain and stock

# Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

None

## **Impact on Environmental Ratings**

Checked boxes indicate the status of environmental ratings following implementation of this change. If below boxes are checked, there are no changes to the associated environmental ratings.

RoHS	REACH	Green Status	IEC 62474
No Change	No Change	No Change	No Change

# Changes to product identification resulting from this PCN:

None

## **Product Affected:**

ISO1042BQDWVQ1	UCC23313BQDWYRQ1	UCC23511QDWYQ1	UCC23513BQDWYRQ1
ISO1042QDWVQ1	UCC23313QDWYQ1	UCC23511QDWYRQ1	UCC23513QDWYQ1
ISO1042QDWVRQ1	UCC23313QDWYRQ1	UCC23513BQDWYQ1	UCC23513QDWYRQ1
UCC23313BQDWYQ1			

# Automotive Qualification Summary (As per AEC-Q100 Rev. J and JEDEC Guidelines)

# 8DWV/6DWY ISO.2 full PCC wire qualification Approve Date 23-February-2024

#### **Product Attributes**

Attributes	Qual Device:	QBS Package Reference:	QBS Package Reference:	QBS Process Reference:	QBS Package Reference:	QBS Package Reference:	QBS Package Reference:
Attributes	UCC23513DWY	UCC23513QDWYRQ1	UCC23513QDWYQ1	ISO7741FEDWRQ1	SN5350MCQDWVRQ1	ISO6763QDWRQ1	UCC21540QDWKRQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 0	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125	-40 to 150	-40 to 125	-40 to 125	-40 to 125
Product Function	Power Management	Power Management	Power Management	Interface	Power Management	Interface	Power Management
Wafer Fab Supplier	MH8, MH8	RFAB, RFAB	RFAB, RFAB	MH8, MH8	RFAB, RFAB	RFAB, RFAB	MH8, MH8, MH8
Assembly Site	TAI	MLA	TAI	TAI	TAI	MLA	TAI
Package Group	SOIC	SOIC	SOIC	SOIC	SOIC	SOIC	SOIC
Package Designator	DWY	DWY	DWY	DW	DWV	DW	DWK
Pin Count	6	6	6	16	8	16	14

- QBS: Qual By Similarity
   Qual Device UCC23513DWY is qualified at MSL2 260C

#### Qualification Results

Type	,	Test Spec	Min	SS /	Test Name	Condition	Duration	Qual Device:	QBS Package Reference:	QBS Package Reference:	QBS Process Reference:	QBS Package Reference:	QBS Package Reference:	QBS Package Reference:
			Qty	Lot			20000000	UCC23513DWY	UCC23513QDWYRQ1	UCC23513QDWYQ1	ISO7741FEDWRQ1	SN5350MCQDWVRQ1	ISO6763QDWRQ1	UCC21540QDWKRQ1
Test Group	A - Acce	elerated Enviro	nment St	ress Tes	its									
PC	A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL2 260C			1/924/0	3/828/0		3/462/0	3/828/0	1/828/0
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	96 Hours		3/231/0	3/231/0		na .	3/231/0	3/231/0

Туре		Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device:	QBS Package Reference: UCC23513QDWYRQ1	QBS Package Reference: UCC23513QDWYQ1	QBS Process Reference: ISO7741FEDWRQ1	QBS Package Reference: SN5350MCQDWVRQ1	QBS Package Reference: ISO6763QDWRQ1	QBS Package Reference: UCC21540QDWKRQ1
AC/UHAST	A3	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Autoclave	121C/15psig	96 Hours		3/231/0	3/231/0		3/231/0	3/231/0	3/231/0
тс	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles		3/231/0	3/231/0		3/231/0	3/231/0	3/231/0
TC-BP	A4	MIL-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull				1/5/0	1/5/0		1/5/0	1/5/0	1/5/0
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	150C	1000 Hours		3/231/0	-			3/135/0	3/135/0
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	175C	500 Hours	-	-	3/135/0				
Test Group I	B - Acce	lerated Lifetime	e Simula	tion Tes	ts			6 *						76
HTOL	B1	JEDEC JESD22- A108	3	77	Life Test	125C	1000 Hours		-	3/231/0	-			21
HTOL	B1	JEDEC JESD22- A108	3	77	Life Test	150C	1000 Hours	-		-	3/231/0			
ELFR	B2	AEC Q100- 008	3	800	Early Life Failure Rate	125C	48 Hours	•		3/2400/0			•	•
ELFR	B2	AEC Q100- 008	3	800	Early Life Failure Rate	150C	48 Hours	-	-	-	3/2400/0			
Test Group	C - Pack	age Assembly	Integrity	Tests									·	
WBS	C1	AEC Q100- 001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	3/90/0	3/90/0		3/90/0	3/90/0	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	3/90/0	3/90/0		3/90/0	3/90/0	3/90/0
SD	СЗ	JEDEC J- STD-002	1	15	PB Solderability	>95% Lead Coverage				1/15/0	1/15/0			
SD	С3	JEDEC J- STD-002	1	15	PB-Free Solderability	>95% Lead Coverage				1/15/0	1/15/0			.:
PD	C4	JEDEC JESD22- B100 and B108	3	10	Physical Dimensions	Cpk>1.67		-	3/30/0	3/30/0	3/30/0	3/30/0		
Test Group I	D - Die F	abrication Relia	ability Te	sts			8	0	50.					ie.
ЕМ	D1	JESD61	-		Electromigration			Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Туре	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name	Condition	Duration	Qual Device:	QBS Package Reference:	QBS Package Reference:	QBS Process Reference:	QBS Package Reference:	QBS Package Reference:	QBS Package Reference:
TDDB	D2	JESD35			Time Dependent Dielectric			Completed Per Process	Completed Per Process Technology	Completed Per Process Technology	Completed Per Process Technology	SN5350MCQDWVRQ1  Completed Per Process Technology	Completed Per Process Technology	Completed Per Process Technology
		JESD60 &			Breakdown  Hot Carrier			Technology Requirements Completed Per Process	Requirements  Completed Per	Requirements  Completed Per	Requirements  Completed Per Process	Requirements  Completed Per	Requirements  Completed Per	Requirements  Completed Per
HCI	D3	28	•	-	Injection		•	Technology Requirements Completed Per	Process Technology Requirements	Process Technology Requirements	Technology Requirements	Process Technology Requirements	Process Technology Requirements	Process Technology Requirements
ВТІ	D4	-	-	-	Bias Temperature Instability		-	Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5				Stress Migration		-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group I	E - Electi	rical Verification	n Tests											
ESD	E2	AEC Q100- 002	1	3	ESD HBM		2000 Volts	-	-	1/3/0	1/3/0	1/3/0		
ESD	E3	AEC Q100- 011	1	3	ESD CDM		750 Volts	-		1/3/0	1/3/0	1/3/0		
LU	E4	AEC Q100- 004	1	6	Latch-Up	Per AEC Q100-004		-		1/6/0	1/6/0	1/6/0		
ED	E5	AEC Q100- 009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-		1/30/0	3/90/0	3/90/0	3/90/0	3/90/0	3/90/0
Additional To	ests													

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Blased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
  The following are equivalent HTQL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
  The following are equivalent HTSL options based on an activation energy of 0.7eV: 155C/1k Hours, and 170C/420 Hours
  The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -65C/150C/500 Cycles

- Grade 0 (or E): -40C to +150C Grade 1 (or Q): -40C to +125C Grade 2 (or T): -40C to +105C Grade 3 (or I): -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL, ED
   Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
   Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

Ti Qualification ID: R-CHG-2310-004

# R-CHG-2203-083 Q100 Qual memo

TI Information Selective Disclosure

# Automotive Qualification Summary (As per AEC-Q100 Rev. H and JEDEC Guidelines)

# ISO672XQDWVRQ1/F G2ISO672XB0Z RFAB offload Full PCC - AUTOMOTIVE Approve Date 21-February-2024

#### **Product Attributes**

Attributes	Qual Device: ISO6721QDWVRQ1	QBS Process Reference:  UCC23513QDWYQ1	QBS Package Reference:	QBS Package Reference: <u>AMC1311CQDWVRQ1</u>
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125	-40 to 125
Product Function	Interface	Power Management	Interface	Signal Chain
Wafer Fab Supplier	RFAB, RFAB	RFAB, RFAB	RFAB, RFAB	AIZU, AIZU, MH8, MH8
Assembly Site	MLA	TAI	MLA	MLA
Package Group	SOIC	SOIC	SOIC	SOIC
Package Designator	DWV	DWY	DW	DWV
Pin Count	8	6	16	8

- QBS: Qual By Similarity
- Qual Device ISO6721QDWVRQ1 is qualified at MSL2 260C
- Qual Device ISO6721FQDWVRQ1 is qualified at MSL2 260C
- Qual Device ISO6720QDWVRQ1 is qualified at MSL2 260C
- Qual Device ISO6720FQDWVRQ1 is qualified at MSL2 260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Туре		Test Spec	Min Lot	SS /	Test Name	Condition	Duration	Qual Device:	QBS Process Reference:	QBS Package Reference:	QBS Package Reference:
			Qty	Lot				ISO6721QDWVRQ1	UCC23513QDWYQ1	ISO6763QDWRQ1	AMC1311CQDWVRQ
Test Group	A - Acc	elerated Enviror	ment S	tress Te	sts						
PC	A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL2 260C		1/154/0		3/828/0	
PC	A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL3 260C	-	-	-		3/828/0
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	96 Hours		-	3/231/0	3/231/0
AC/UHAST	A3	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Autoclave	121C/15psig	96 Hours	1/77/0		3/231/0	-
AC/UHAST	A3	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Unbiased HAST	130C/85%RH	96 Hours			-	3/231/0
тс	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	1/77/0	-	3/231/0	3/231/0
TC-BP	A4	MIL-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull			1/5/0	-	1/5/0	1/5/0
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	150C	1000 Hours		-	3/135/0	-
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	175C	500 Hours	-	-		3/135/0

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device:	QBS Process Reference: UCC23513QDWYQ1	QBS Package Reference: ISO6763QDWRQ1	QBS Package Reference: AMC1311CQDWVRQ
HTOL	B1	JEDEC JESD22- A108	3	77	Life Test	125C	1000 Hours	-	3/231/0	-	-
ELFR	B2	AEC Q100- 008	3	800	Early Life Failure Rate	125C	48 Hours	-	3/2400/0		
Test Grou	p C - Pac	kage Assembly	Integrity	Tests	30.		700		120		Šie.
WBS	C1	AEC Q100- 001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	-	3/90/0	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	-	3/90/0	3/90/0
SD	СЗ	JEDEC J- STD-002	1	15	PB Solderability	>95% Lead Coverage	-	-			1/15/0
SD	СЗ	JEDEC J- STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	-	-	1/15/0
PD	C4	JEDEC JESD22- B100 and B108	3	10	Physical Dimensions	Cpk>1.67		-			3/30/0
Test Grou	p D - Die	Fabrication Relia	ability To	ests							
ЕМ	D1	JESD61			Electromigration			Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-		Time Dependent Dielectric Breakdown			Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
нсі	D3	JESD60 & 28			Hot Carrier Injection		-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
ВТІ	D4				Bias Temperature Instability			Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements

Туре		Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device:	QBS Process Reference: UCC23513QDWYQ1	QBS Package Reference: ISO6763QDWRQ1	QBS Package Reference: AMC1311CQDWVRQ1
SM	D5				Stress Migration	-		Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group	E - Elec	trical Verificatio	n Tests								
ESD	E2	AEC Q100- 002	1	3	ESD HBM	-	2000 Volts	1/3/0	1/3/0	-	1/3/0
ESD	E3	AEC Q100- 011	1	3	ESD CDM		750 Volts	1/3/0	1/3/0	-	1/3/0
LU	E4	AEC Q100- 004	1	6	Latch-Up	Per AEC Q100-004		1/6/0	1/6/0	-	1/6/0
ED	E5	AEC Q100- 009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold		1/30/0	3/90/0	3/90/0	1/30/0

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
  The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

- Grade 0 (or E): -40C to +150C
- Grade 1 (or Q): -40C to +125C
- Grade 2 (or T): -40C to +105C
- Grade 3 (or I): -40C to +85C

#### E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL, ED
- Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

TI Qualification ID: R-CHG-2203-083

# R-CHG-2208-024 Q100 Qual memo

TI Information Selective Disclosure

# Automotive Qualification Summary (As per AEC-Q100 Rev. H and JEDEC Guidelines)

## RFAB LBC8LVISO.1 Second Source Approve Date 20-December-2023

### **Product Attributes**

Attributes	Qual Device:	QBS Package, Process Reference:	QBS Package Reference:
Attributes	SN5350MCQDWVRQ1	<u>UCC23513QDWYQ1</u>	UCC21540QDWKRQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125
Product Function	Power Management	Power Management	Power Management
Wafer Fab Supplier	RFAB, RFAB	RFAB, RFAB	MH8, MH8, MH8
Assembly Site	TAI	TAI	TAI
Package Group	SOIC	SOIC	SOIC
Package Designator	DWV	DWY	DWK
Pin Count	8	6	14

- · QBS: Qual By Similarity
- Qual Device SN5350MCQDWVRQ1 is qualified at MSL2 260C

#### **Qualification Results**

Туре	#	Test Spec	Min Lot	SS /	Test Name	Condition	Duration	Qual Device:	QBS Package, Process Reference:	QBS Package Reference:
			Qty					SN5350MCQDWVRQ1	UCC23513QDWYQ1	UCC21540QDWKRQ1
Test Group	A - Acce	elerated Environ	ment St	ress Tes	sts					
PC	A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL2 260C	-	3/Pass	3/Pass	1/Pass
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	96 Hours	-	3/231/0	1/77/0
AC/UHAST	А3	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Autoclave	121C/15psig	96 Hours	3/231/0	3/231/0	3/231/0
тс	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	3/231/0	3/231/0	1/77/0
TC-BP	A4	MIL-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull	-	-	1/5/0	-	-
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	150C	1000 Hours	-	-	1/45/0
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	175C	500 Hours	-	3/135/0	-
Test Group	B - Acce	elerated Lifetime	Simula	tion Tes	ts					
HTOL	B1	JEDEC JESD22- A108	3	77	Life Test	125C	1000 Hours	-	3/231/0	-
ELFR	B2	AEC Q100- 008	3	800	Early Life Failure Rate	125C	48 Hours	-	3/2400/0	-

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: <u>SN5350MCQDWVRQ1</u>	QBS Package, Process Reference: UCC23513QDWYQ1	QBS Package Reference: <u>UCC21540QDWKRQ1</u>
Test Group	C - Pack	age Assembly	Integrity	Tests						
WBS	C1	AEC Q100- 001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	3/90/0	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	3/90/0	3/90/0
SD	СЗ	JEDEC J- STD-002	1	15	PB Solderability	>95% Lead Coverage	-	-	1/15/0	-
SD	СЗ	JEDEC J- STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	1/15/0	-
PD	C4	JEDEC JESD22- B100 and B108	3	10	Physical Dimensions	Cpk>1.67	-	3/30/0	-	-
Test Group	D - Die F	abrication Relia	ability Te	sts						
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
нсі	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
вті	D4	-	-	-	Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device:	QBS Package, Process Reference:	QBS Package Reference:
Toot Group I	E Elect	rical Varification	Tocto						UCC23513QDWYQ1	UCC21540QDWKRQ1
		rical Verification AEC Q100-					2000			
ESD	E2	002	1	3	ESD HBM	-	Volts	1/3/0	-	-
ESD	E3	AEC Q100- 011	1	3	ESD CDM	-	500 Volts	1/3/0	-	-
LU	E4	AEC Q100- 004	1	6	Latch-Up	Per AEC Q100-004	-	1/6/0	-	-
ED	E5	AEC Q100- 009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	3/90/0	-	-

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

- Grade 0 (or E): -40C to +150C
- Grade 1 (or Q): -40C to +125C
- Grade 2 (or T): -40C to +105C
- Grade 3 (or I): -40C to +85C

#### E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- · Room/Hot/Cold : HTOL, ED
- Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: <a href="http://www.ti.com/">http://www.ti.com/</a>

TI Qualification ID: R-CHG-2208-024

# Automotive Qualification Summary (As per AEC and JEDEC Guidelines)

#### Q006 SOIC at MLA and TAI Approve Date 19-OCTOBER -2023

Attributes	Qual Device: <u>ISO6763QDWRQ1</u>	Qual Device: UCC21540QDWKRQ1	QBS Package Reference:  PUCC21550ADWKR
Automotive Grade Level	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125
Wafer Fab Supplier	RFAB, RFAB	MH8, MH8, MH8	DMOS6, DMOS6, MH8
Assembly Site	MLA	TAI	TAI
Package Group	SOIC	SOIC	SOIC
Package Designator	DW	DWK	DWK
Pin Count	16	14	14

#### **Qualification Results**

Туре	#	Test Spec	Min Lot	SS /	Test Name	Condition	Duration	Qual Device: ISO6763QDWRQ1	Qual Device: UCC21540QDWKRQ1	QBS Reference: PUCC21550ADWKR
Test G	roup A - /	Accelerated Env	Qty ironmen	t Stress	Tests	L	<u> </u>			
PC	A1	JEDEC J- STD-020 JESD22-A113	3	77	Preconditioning	MSL2 260C	-	3/597/0	1/199/0	-
PC	A1	JEDEC J- STD-020 JESD22-A113	3	77	Preconditioning	MSL3 260C	-	-	-	3/693/0
PC	A1.1	-	3	22	SAM Precon Pre	Review for delamination	-	3/66/0	1/22/0	3/66/0
PC	A1.2	-	3	22	SAM Precon Post	Review for delamination	-	3/66/0	1/22/0	3/66/0
HAST	A2.1	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	3/231/0	1/77/0	3/231/0
HAST	A2.1.2	-	3	1	Cross Section, post bHAST, 1X	Post stress cross section	Completed	3/3/0	1/1/0	-
HAST	A2.1.3	-	3	3	Wire Bond Shear, post bHAST, 1X	Post stress	-	3/9/0	1/3/0	3/9/0
HAST	A2.1.4	-	3	3	Bond Pull over Stitch, post bHAST, 1X	Post stress	-	3/9/0	1/3/0	3/9/0
HAST	A2.1.5	-	3	3	Bond Pull over Ball, post bHAST, 1X	Post stress	-	3/9/0	1/3/0	3/9/0
HAST	A2.2	JEDEC JESD22-A110	3	70	Biased HAST	130C/85%RH	192 Hours	3/210/0	1/70/0	3/210/0
HAST	A2.2.1	-	3	22	SAM Analysis, post bHAST 2X	Review for delamination	Completed	3/66/0	1/22/0	3/66/0
HAST	A2.2.2	-	3	1	Cross Section, post bHAST, 2X	Post stress cross section	Completed	3/3/0	1/1/0	3/3/0
HAST	A2.2.3	-	3	3	Wire Bond Shear, post bHAST, 2X	Post stress	-	3/9/0	1/3/0	3/9/0

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ISO6763QDWRQ1	Qual Device: <u>UCC21540QDWKRQ1</u>	QBS Reference: PUCC21550ADWKR
HAST	A2.2.4	-	3	3	Bond Pull over Stitch, post bHAST, 2X	Post stress	-	3/9/0	1/3/0	3/9/0
HAST	A2.2.5	-	3	3	Bond Pull over Ball, post bHAST, 2X	Post stress	-	3/9/0	1/3/0	3/9/0
тс	A4.1	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-55C/150C	1000 Cycles	-	-	3/231/0
тс	A4.1	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	3/231/0	1/77/0	-
тс	A4.1.1	-	3	22	SAM Analysis, post TC 1X	Review for delamination	Completed	3/66/0	1/22/0	3/66/0
тс	A4.1.2	-	3	1	Cross Section, post TC, 1X	Post stress cross section	Completed	3/3/0	1/1/0	-
тс	A4.1.3	-	3	3	Wire Bond Shear, post TC, 1X	Post stress	-	3/9/0	1/3/0	3/9/0
тс	A4.1.4	-	3	3	Bond Pull over Stitch, post TC, 1X	Post stress	-	3/9/0	1/3/0	3/9/0
тс	A4.1.5	-	3	3	Bond Pull over Ball, post TC, 1X	Post stress	-	3/9/0	1/3/0	3/9/0
тс	A4.2	JEDEC JESD22-A104 and Appendix 3	3	70	Temperature Cycle	-55C/150C	2000 Cycles	-	-	3/210/0
тс	A4.2	JEDEC JESD22-A104 and Appendix 3	3	70	Temperature Cycle	-65C/150C	1000 Cycles	3/210/0	1/70/0	-
TC	A4.2.1	-	3	22	SAM Analysis, post TC, 2X	Review for delamination	Completed	3/66/0	1/22/0	3/66/0

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ISO6763QDWRQ1	Qual Device: UCC21540QDWKRQ1	QBS Reference: PUCC21550ADWKR
тс	A4.2.2	-	3	1	Cross Section, post TC, 2X	Post stress cross section	Completed	3/3/0	1/1/0	3/3/0
тс	A4.2.3	-	3	3	Wire Bond Shear, post TC, 2X	Post stress	-	3/9/0	1/3/0	3/9/0
тс	A4.2.4	-	3	3	Bond Pull over Stitch, post TC, 2X	Post stress	-	3/9/0	1/3/0	3/9/0
тс	A4.2.5	-	3	3	Bond Pull over Ball, post TC, 2X	Post stress	-	3/9/0	1/3/0	3/9/0
HTSL	A6.1	JEDEC JESD22-A103	3	45	High Temperature Storage Life	150C	1000 Hours	3/135/0	1/45/0	-
HTSL	A6.1	JEDEC JESD22-A103	3	45	High Temperature Storage Life	175C	500 Hours	-	-	3/231/0
HTSL	A6.1.1	-	3	1	Cross Section, post HTSL, 1X	Post stress cross section	Completed	3/3/0	1/1/0	3/3/0
HTSL	A6.2	JEDEC JESD22-A103	3	44	High Temperature Storage Life	150C	2000 Hours	3/132/0	1/44/0	-
HTSL	A6.2	JEDEC JESD22-A103	3	44	High Temperature Storage Life	175C	1000 Hours	-	-	3/228/0
HTSL	A6.2.1	-	3	1	Cross Section, post HTSL, 2X	Post stress cross section	Completed	3/3/0	1/1/0	3/3/0
Test G	roup C - F	Package Asseml	bly Integ	rity Test	s					
WBS	C1	AEC Q100- 001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	3/90/0	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	3/90/0	3/90/0

- QBS: Qual By Similarity
- Qual Device ISO6763QDWRQ1 is qualified at MSL2 260C
- Qual Device UCC21540QDWKRQ1 is qualified at MSL3 260C
- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -65C/150C/500 Cycles

- Grade 0 (or E): -40C to +150C
- Grade 1 (or Q): -40C to +125C
   Grade 2 (or T): 40C to +10EC
- Grade 2 (or T): -40C to +105C
   Grade 3 (or I): -40C to +85C

### E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL, ED
- Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: <a href="http://www.ti.com/">http://www.ti.com/</a>

TI Qualification ID: R-CHG-2303-105

## R-CHG-2310-004 Q006 Qual memo

# Automotive Qualification Summary (As per AEC and JEDEC Guidelines)

### Q006 SOIC at MLA and TAI Approve Date 19-OCTOBER -2023

Attributes	Qual Device:	Qual Device:	QBS Package Reference:
Attributes	<u>ISO6763QDWRQ1</u>	UCC21540QDWKRQ1	PUCC21550ADWKR
Automotive Grade Level	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125
Wafer Fab Supplier	RFAB, RFAB	MH8, MH8, MH8	DMOS6, DMOS6, MH8
Assembly Site	MLA	TAI	TAI
Package Group	SOIC	SOIC	SOIC
Package Designator	DW	DWK	DWK
Pin Count	16	14	14

### **Qualification Results**

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ISO6763QDWRQ1	Qual Device: UCC21540QDWKRQ1	QBS Reference: PUCC21550ADWKR
Test G	roup A - /	Accelerated Env	ironmen	t Stress	Tests					
PC	A1	JEDEC J- STD-020 JESD22-A113	3	77	Preconditioning	MSL2 260C	-	3/597/0	1/199/0	-
PC	A1	JEDEC J- STD-020 JESD22-A113	3	77	Preconditioning	MSL3 260C	-	-	-	3/693/0
PC	A1.1	-	3	22	SAM Precon Pre	Review for delamination	-	3/66/0	1/22/0	3/66/0
PC	A1.2	-	3	22	SAM Precon Post	Review for delamination	-	3/66/0	1/22/0	3/66/0
HAST	A2.1	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	3/231/0	1/77/0	3/231/0
HAST	A2.1.2	-	3	1	Cross Section, post bHAST, 1X	Post stress cross section	Completed	3/3/0	1/1/0	-
HAST	A2.1.3	-	3	3	Wire Bond Shear, post bHAST, 1X	Post stress	-	3/9/0	1/3/0	3/9/0
HAST	A2.1.4	-	3	3	Bond Pull over Stitch, post bHAST, 1X	Post stress	-	3/9/0	1/3/0	3/9/0
HAST	A2.1.5	-	3	3	Bond Pull over Ball, post bHAST, 1X	Post stress	-	3/9/0	1/3/0	3/9/0
HAST	A2.2	JEDEC JESD22-A110	3	70	Biased HAST	130C/85%RH	192 Hours	3/210/0	1/70/0	3/210/0
HAST	A2.2.1	-	3	22	SAM Analysis, post bHAST 2X	Review for delamination	Completed	3/66/0	1/22/0	3/66/0
HAST	A2.2.2	-	3	1	Cross Section, post bHAST, 2X	Post stress cross section	Completed	3/3/0	1/1/0	3/3/0
HAST	A2.2.3	-	3	3	Wire Bond Shear, post bHAST, 2X	Post stress	-	3/9/0	1/3/0	3/9/0

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ISO6763QDWRQ1	Qual Device: <u>UCC21540QDWKRQ1</u>	QBS Reference: PUCC21550ADWKR
HAST	A2.2.4	-	3	3	Bond Pull over Stitch, post bHAST, 2X	Post stress	-	3/9/0	1/3/0	3/9/0
HAST	A2.2.5	-	3	3	Bond Pull over Ball, post bHAST, 2X	Post stress	-	3/9/0	1/3/0	3/9/0
тс	A4.1	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-55C/150C	1000 Cycles	-	-	3/231/0
тс	A4.1	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	3/231/0	1/77/0	-
тс	A4.1.1	-	3	22	SAM Analysis, post TC 1X	Review for delamination	Completed	3/66/0	1/22/0	3/66/0
тс	A4.1.2	-	3	1	Cross Section, post TC, 1X	Post stress cross section	Completed	3/3/0	1/1/0	-
тс	A4.1.3	-	3	3	Wire Bond Shear, post TC, 1X	Post stress	-	3/9/0	1/3/0	3/9/0
тс	A4.1.4	-	3	3	Bond Pull over Stitch, post TC, 1X	Post stress	-	3/9/0	1/3/0	3/9/0
тс	A4.1.5	-	3	3	Bond Pull over Ball, post TC, 1X	Post stress	-	3/9/0	1/3/0	3/9/0
тс	A4.2	JEDEC JESD22-A104 and Appendix 3	3	70	Temperature Cycle	-55C/150C	2000 Cycles	-	-	3/210/0
тс	A4.2	JEDEC JESD22-A104 and Appendix 3	3	70	Temperature Cycle	-65C/150C	1000 Cycles	3/210/0	1/70/0	-
тс	A4.2.1	-	3	22	SAM Analysis, post TC, 2X	Review for delamination	Completed	3/66/0	1/22/0	3/66/0

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ISO6763QDWRQ1	Qual Device: UCC21540QDWKRQ1	QBS Reference: PUCC21550ADWKR
тс	A4.2.2	-	3	1	Cross Section, post TC, 2X	Post stress cross section	Completed	3/3/0	1/1/0	3/3/0
тс	A4.2.3	-	3	3	Wire Bond Shear, post TC, 2X	Post stress	-	3/9/0	1/3/0	3/9/0
TC	A4.2.4	-	3	3	Bond Pull over Stitch, post TC, 2X	Post stress	-	3/9/0	1/3/0	3/9/0
тс	A4.2.5	-	3	3	Bond Pull over Ball, post TC, 2X	Post stress	-	3/9/0	1/3/0	3/9/0
HTSL	A6.1	JEDEC JESD22-A103	3	45	High Temperature Storage Life	150C	1000 Hours	3/135/0	1/45/0	-
HTSL	A6.1	JEDEC JESD22-A103	3	45	High Temperature Storage Life	175C	500 Hours	-	-	3/231/0
HTSL	A6.1.1	-	3	1	Cross Section, post HTSL, 1X	Post stress cross section	Completed	3/3/0	1/1/0	3/3/0
HTSL	A6.2	JEDEC JESD22-A103	3	44	High Temperature Storage Life	150C	2000 Hours	3/132/0	1/44/0	-
HTSL	A6.2	JEDEC JESD22-A103	3	44	High Temperature Storage Life	175C	1000 Hours	-	-	3/228/0
HTSL	A6.2.1	-	3	1	Cross Section, post HTSL, 2X	Post stress cross section	Completed	3/3/0	1/1/0	3/3/0
Test G	roup C - F	Package Assemi	bly Integ	rity Test	s					
WBS	C1	AEC Q100- 001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	3/90/0	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	3/90/0	3/90/0

- QBS: Qual By Similarity
- Qual Device ISO6763QDWRQ1 is qualified at MSL2 260C
- Qual Device UCC21540QDWKRQ1 is qualified at MSL3 260C
- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

- Grade 0 (or E): -40C to +150C
- Grade 1 (or Q): -40C to +125C
- Grade 2 (or T): -40C to +105C
- Grade 3 (or I): -40C to +85C

#### E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL, ED
- Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: <a href="http://www.ti.com/">http://www.ti.com/</a>

TI Qualification ID: R-CHG-2303-105

# R-CHG-2208-024 Q006 Qual memo

# Automotive Qualification Summary (As per AEC and JEDEC Guidelines)

# Q006 SOIC at MLA and TAI Approve Date 19-OCTOBER -2023

Attributes	Qual Device: ISO6763QDWRQ1	Qual Device: <u>UCC21540QDWKRQ1</u>	QBS Package Reference: <u>PUCC21550ADWKR</u>	
Automotive Grade Level	Grade 1	Grade 1	Grade 1	
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125	
Wafer Fab Supplier	RFAB, RFAB	MH8, MH8, MH8	DMOS6, DMOS6, MH8	
Assembly Site	MLA	TAI	TAI	
Package Group	SOIC	SOIC	SOIC	
Package Designator	DW	DWK	DWK	
Pin Count	16	14	14	

### **Qualification Results**

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ISO6763QDWRQ1	Qual Device: UCC21540QDWKRQ1	QBS Reference: PUCC21550ADWKR
Test G	roup A - A	Accelerated Env	ironmen	t Stress	Tests				'	
PC	A1	JEDEC J- STD-020 JESD22-A113	3	77	Preconditioning	MSL2 260C	-	3/597/0	1/199/0	-
PC	A1	JEDEC J- STD-020 JESD22-A113	3	77	Preconditioning	MSL3 260C	-	-	-	3/693/0
PC	A1.1	-	3	22	SAM Precon Pre	Review for delamination	-	3/66/0	1/22/0	3/66/0
PC	A1.2	-	3	22	SAM Precon Post	Review for delamination	-	3/66/0	1/22/0	3/66/0
HAST	A2.1	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	3/231/0	1/77/0	3/231/0
HAST	A2.1.2	-	3	1	Cross Section, post bHAST, 1X	Post stress cross section	Completed	3/3/0	1/1/0	-
HAST	A2.1.3	-	3	3	Wire Bond Shear, post bHAST, 1X	Post stress	-	3/9/0	1/3/0	3/9/0
HAST	A2.1.4	-	3	3	Bond Pull over Stitch, post bHAST, 1X	Post stress	-	3/9/0	1/3/0	3/9/0
HAST	A2.1.5	-	3	3	Bond Pull over Ball, post bHAST, 1X	Post stress	-	3/9/0	1/3/0	3/9/0
HAST	A2.2	JEDEC JESD22-A110	3	70	Biased HAST	130C/85%RH	192 Hours	3/210/0	1/70/0	3/210/0
HAST	A2.2.1	-	3	22	SAM Analysis, post bHAST 2X	Review for delamination	Completed	3/66/0	1/22/0	3/66/0
HAST	A2.2.2	-	3	1	Cross Section, post bHAST, 2X	Post stress cross section	Completed	3/3/0	1/1/0	3/3/0
HAST	A2.2.3	-	3	3	Wire Bond Shear, post bHAST, 2X	Post stress	-	3/9/0	1/3/0	3/9/0

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ISO6763QDWRQ1	Qual Device: <u>UCC21540QDWKRQ1</u>	QBS Reference: PUCC21550ADWKR
HAST	A2.2.4	-	3	3	Bond Pull over Stitch, post bHAST, 2X	Post stress	-	3/9/0	1/3/0	3/9/0
HAST	A2.2.5	-	3	3	Bond Pull over Ball, post bHAST, 2X	Post stress	-	3/9/0	1/3/0	3/9/0
тс	A4.1	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-55C/150C	1000 Cycles	-	-	3/231/0
тс	A4.1	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	3/231/0	1/77/0	-
тс	A4.1.1	-	3	22	SAM Analysis, post TC 1X	Review for delamination	Completed	3/66/0	1/22/0	3/66/0
тс	A4.1.2	-	3	1	Cross Section, post TC, 1X	Post stress cross section	Completed	3/3/0	1/1/0	-
тс	A4.1.3	-	3	3	Wire Bond Shear, post TC, 1X	Post stress	-	3/9/0	1/3/0	3/9/0
тс	A4.1.4	-	3	3	Bond Pull over Stitch, post TC, 1X	Post stress	-	3/9/0	1/3/0	3/9/0
тс	A4.1.5	-	3	3	Bond Pull over Ball, post TC, 1X	Post stress	-	3/9/0	1/3/0	3/9/0
тс	A4.2	JEDEC JESD22-A104 and Appendix 3	3	70	Temperature Cycle	-55C/150C	2000 Cycles	-	-	3/210/0
тс	A4.2	JEDEC JESD22-A104 and Appendix 3	3	70	Temperature Cycle	-65C/150C	1000 Cycles	3/210/0	1/70/0	-
тс	A4.2.1	-	3	22	SAM Analysis, post TC, 2X	Review for delamination	Completed	3/66/0	1/22/0	3/66/0

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ISO6763QDWRQ1	Qual Device: UCC21540QDWKRQ1	QBS Reference: PUCC21550ADWKR
тс	A4.2.2	-	3	1	Cross Section, post TC, 2X	Post stress cross section	Completed	3/3/0	1/1/0	3/3/0
тс	A4.2.3	-	3	3	Wire Bond Shear, post TC, 2X	Post stress	-	3/9/0	1/3/0	3/9/0
тс	A4.2.4	-	3	3	Bond Pull over Stitch, post TC, 2X	Post stress	-	3/9/0	1/3/0	3/9/0
тс	A4.2.5	-	3	3	Bond Pull over Ball, post TC, 2X	Post stress	-	3/9/0	1/3/0	3/9/0
HTSL	A6.1	JEDEC JESD22-A103	3	45	High Temperature Storage Life	150C	1000 Hours	3/135/0	1/45/0	-
HTSL	A6.1	JEDEC JESD22-A103	3	45	High Temperature Storage Life	175C	500 Hours	-	-	3/231/0
HTSL	A6.1.1	-	3	1	Cross Section, post HTSL, 1X	Post stress cross section	Completed	3/3/0	1/1/0	3/3/0
HTSL	A6.2	JEDEC JESD22-A103	3	44	High Temperature Storage Life	150C	2000 Hours	3/132/0	1/44/0	-
HTSL	A6.2	JEDEC JESD22-A103	3	44	High Temperature Storage Life	175C	1000 Hours	-	-	3/228/0
HTSL	A6.2.1	-	3	1	Cross Section, post HTSL, 2X	Post stress cross section	Completed	3/3/0	1/1/0	3/3/0
Test Group C - Package Assembly Integrity Tests										
WBS	C1	AEC Q100- 001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	3/90/0	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	3/90/0	3/90/0

- QBS: Qual By Similarity
- Qual Device ISO6763QDWRQ1 is qualified at MSL2 260C
- Qual Device UCC21540QDWKRQ1 is qualified at MSL3 260C
- · Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

- Grade 0 (or E): -40C to +150C
- Grade 1 (or Q): -40C to +125C
- Grade 2 (or T): -40C to +105C
- Grade 3 (or I): -40C to +85C

#### E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL, ED
- Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

TI Qualification ID: R-CHG-2303-105

# ZVEI ID: SEM-PA-08

For questions regarding this notice, e-mails can be sent to Change Management team or your local Field Sales Representative.

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